



**DSS3540M** 

### 40V PNP LOW V<sub>CE(sat)</sub> TRANSISTOR

### **Features**

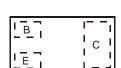
- $BV_{CEO} > -40V$
- I<sub>C</sub> = -500mA High Collector Current
- I<sub>CM</sub> = -1A Peak Pulse Current
- P<sub>D</sub> = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, VCE(sat)
- 0.60mm<sup>2</sup> Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DSS2540M
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability



**Bottom View** 



- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 Terminals: Finish — NiPdAu @4)
- Solderable per MIL-STD-202, Method 208
- Weight: 0.0009 grams (Approximate)



Top View **Device** Schematic

## Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS3540M-7	TD	7	8	3,000
DSS3540M-7B	TD	7	8	10,000

С

F

**Device Symbol** 

R

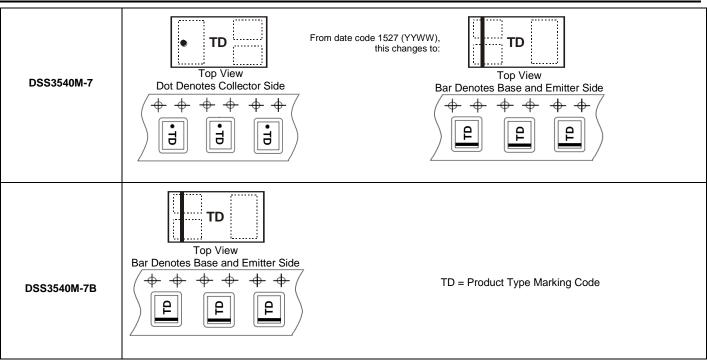
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com.

# Marking Information

Notes:





## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current - Continuous	lc	-500	mA
Peak Pulse Collector Current	I <sub>CM</sub>	-1	A
Peak Base Current	I <sub>BM</sub>	-100	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Dower Dissinction	(Note 5)	400		mW	
Power Dissipation	(Note 6)		1,000		
Thermal Desistance, Junction to Ambient	(Note 5)	310		°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	120	C/W	
Thermal Resistance, Junction to Lead (Note 7)		R <sub>θJL</sub>	120	°C/W	
Operating and Storage and Temperature Ran	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	В

Notes: 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

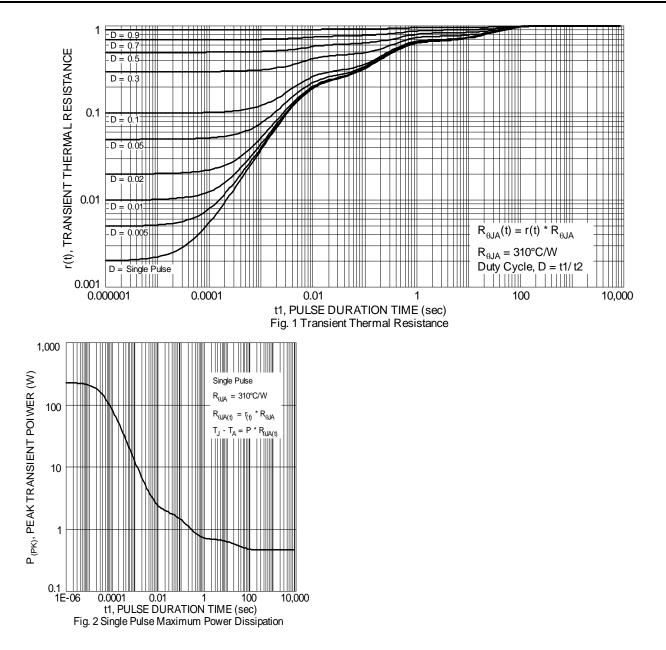
7. Thermal resistance from junction to solder-point (on the exposed collector pad).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



**DSS3540M** 

# **Thermal Characteristics**





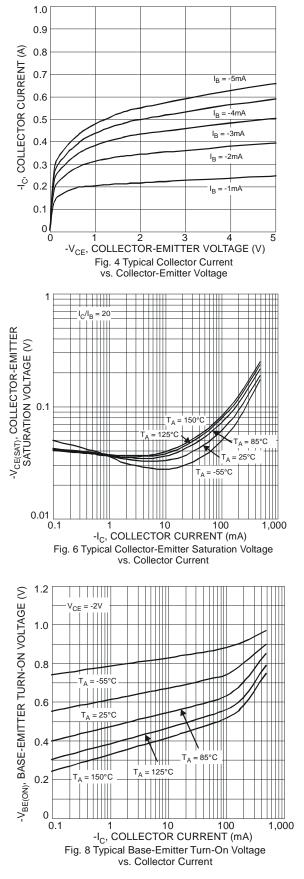
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

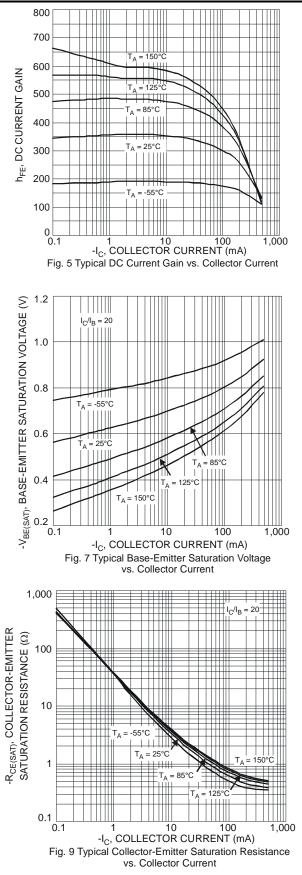
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	Symbol	IVIIII	тур	WIAX	Unit	Test condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	_		V	$I_{\rm C} = -100\mu A$ , $I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BVCBO	-40			V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BVCEO BVEBO	-6			V	$I_E = -100\mu A, I_C = 0$
	DVEBU	Ũ	<u> </u>	-100	nA	$V_{CB} = -30V, I_E = 0$
Collector-Base Cutoff Current	I <sub>CBO</sub>	—	—	-50	μΑ	$V_{CB} = -30V$ , $I_E = 0$ , $T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -5V, I_C = 0$
				-100	nA	$V_{CE} = -30V, V_X = \pm 0.25V$
Collector-Emitter Cutoff Current	ICEX	_	_	-100		$V_{CE} = -30V, V_X = 3V$
Collector-Emitter Cutoff Current	ICES			-100	nA	V <sub>CE</sub> = -30V
ON CHARACTERISTICS (Note 9)						
		200				$V_{CE} = -2V, I_{C} = -10mA$
DC Current Gain	h <sub>FE</sub>	150	—	_		$V_{CE} = -2V, I_{C} = -100mA$
		40				$V_{CE} = -2V, I_{C} = -500mA$
		_	_	-50		$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -0.5 {\rm mA}$
Collector-Emitter Saturation Voltage	N/	_	—	-130	mV	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA
Collector-Emiller Saturation voltage	V <sub>CE(sat)</sub>			-200		I <sub>C</sub> = -200mA, I <sub>B</sub> = -10mA
		_	—	-350		I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Collector-Emitter Saturation Resistance	R <sub>CE(sat)</sub>	_	_	700	mΩ	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	-1.2	V	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Turn On Voltage	V <sub>BE(on)</sub>			-1.1	V	$V_{CE} = -2V, I_{C} = -100mA$
SMALL SIGNAL CHARACTERISTICS	• • • •					
Output Capacitance	C <sub>obo</sub>	_	_	10	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100		_	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA, f = 100MHz
Note: 9. Measured under pulsed conditions. Pul	se width ≤ 300µs. [	Outy cycle ≤	≤2%.			

ter pulsed condition 00µs. Duty cyc



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

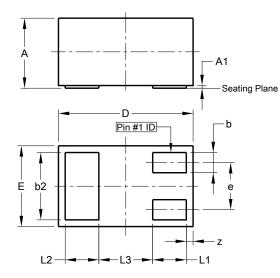






## **Package Outline Dimensions**

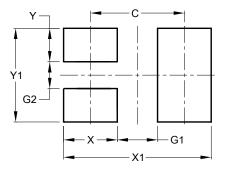
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
ш	0.55	0.675	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	•	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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